

L Number	Hits	Search Text	DB	Time stamp
1	1	5925259.pn.	USPAT; US-PGPUB	2003/01/02 10:11
-	1	4041114.pn.	USPAT; US-PGPUB	2003/01/02 10:11
-	1	5521030.pn.	USPAT; US-PGPUB	2002/08/20 09:46
-	1	4041114.pn.	USPAT; US-PGPUB	2002/08/28 10:59
-	534	stamp and lithograph\$2	USPAT; US-PGPUB	2002/08/30 10:34
-	29	stamp and lithograph\$2 and nano	USPAT; US-PGPUB; EPO; JPO; DERWENT	2002/08/28 11:53
-	577	stamp and lithograph\$2	USPAT; US-PGPUB; EPO; JPO; DERWENT	2002/08/28 14:31
-	1	"4443408".PN.	USPAT	2002/08/28 12:23
-	41085	IBM.as.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2002/08/28 14:33
-	149	IBM.as. and (stamp or indent\$5 or emboss\$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2002/08/28 14:45
-	2	5521030.pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2002/08/28 14:48
-	6843	kumar.in.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2002/08/28 15:22
-	154	microcontact adj printing	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/08/28 15:02
-	115	(microcontact adj printing) not (stamp and lithograph\$2)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/08/28 14:52
-	48	micro adj contact adj printing	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/08/28 15:03
-	36	(micro adj contact adj printing) not ((microcontact adj printing) not (stamp and lithograph\$2))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/08/28 15:03
-	46	kumar.in. and amit	USPAT; US-PGPUB; EPO; JPO; DERWENT	2002/08/28 15:23
-	590	rubber adj stamp	USPAT; US-PGPUB	2002/08/28 16:10
-	659	(rubber or elastomer\$2) adj stamp	USPAT; US-PGPUB	2002/08/28 17:04
-	1	5772905.pn.	USPAT; US-PGPUB	2002/08/28 17:06
-	1	6365059.pn.	USPAT; US-PGPUB	2002/08/28 17:06
-	1	5772905.pn.	USPAT; US-PGPUB	2002/08/30 09:18

-	536	stamp and lithograph\$2	USPAT; US-PGPUB	2002/08/30 10:34
-	19	(stamp and lithograph\$2 ) and (conducting adj polymer)	USPAT; US-PGPUB	2002/08/30 10:35
-	1	5900160.pn.	USPAT; US-PGPUB	2002/08/30 14:48
-	1	5772905.pn.	USPAT; US-PGPUB	2002/08/31 13:05
-	1111	(clean\$4 near4 liquid) and chamber and semiconductor	USPAT; US-PGPUB	2002/12/31 17:52
-	294	((clean\$4 near4 liquid) and chamber and semiconductor) and @ad<19950720	USPAT; US-PGPUB	2002/12/31 18:04
-	57	((((clean\$4 near4 liquid) and chamber and semiconductor) and @ad<19950720) and (clean\$4 near7 etch\$4)	USPAT; US-PGPUB	2002/12/31 18:13
-	30	(((((clean\$4 near4 liquid) and chamber and semiconductor) and @ad<19950720) and (clean\$4 near7 etch\$4)) and (clean\$4 near7 chamber)	USPAT; US-PGPUB	2002/12/31 18:13